

		CT/PROCESS	CHANGE NO	TICE (PCN)	
PCN #: L130 Product Affected		PAG	MEANS OF DISTII ■ Product Mark □ Back Mark □ Date Code □ Other	NGUISHING CHANGED DEVICES: Device Step (prefix prior Date Code) changed from A4 to A5	
Date Effective:	July 3, 2013				
Contact: E-mail:	IDT PCN DESK pcndesk@idt.com		Attachment: Samples: Please cosample r	Yes No ontact your local IDT sales representative for equest	
DESCRIPTION .	AND PURPOSE OF C	HANGE:			
 □ Die Technology □ Wafer Fabrication Process □ Assembly Process □ Equipment □ Material □ Testing ■ Manufacturing Site □ Data Sheet □ Other 		This notification is to advise our customers that IDT has successfully completed the transfer of 74LVCHR162245APAG/8 wafer Fab production from IDT Hillsboro, Oregon (Fab4) to Taiwan Semiconductor Manufacturing Corporation (TSMC). Fab 4 is now closed and all new wafer fab production will be from TSMC. There is no change to ordering part number and device top mark. Refer to Attachment 1 & 2 for details.			
RELIABILITY/ Please refer Attac	QUALIFICATION SU chment 2.	MMARY:			
IDT records indicto grant approval it will be assume IDT reserves the	or request additional in that this change is acc	tten notification of this ch formation. If IDT does no	t receive acknowledgem	nowledgement below or E-Mail ent within 30 days of this notice e date until the inventory	
Customer:			☐ Approval for ship	ments prior to effective date.	
Name/Date:			E-Mail Address:		
Title:			Phone# /Fax#:		
CUSTOMER CO	OMMENTS:				
IDT ACKNOWI	LEDGMENT OF REC	ЕІРТ:			
RECD. BY:			DATE:		



Integrated Device Technology, Inc. 6024 Silver Creek Valley Road San Jose, CA 96138

PRODUCT/PROCESS CHANGE NOTICE (PCN)

ATTACHMENT 1 - PCN # : L1301-01

PCN Type: Wafer Fab Manufacturing Site Change - IDT Fab 4 to TSMC

Data Sheet Change: None

Detail Of Change:

This notification is to advise our customers that IDT has successfully completed the transfer of 74LVCHR162245APAG/8 wafer Fab production from IDT Hillsboro, Oregon (Fab4) to Taiwan Semiconductor Manufacturing Corporation (TSMC).

Fab 4 is now closed and all new wafer fab production will be from TSMC.

There is no change to ordering part number and device top mark.

Characterization data of material manufactured at TSMC is comparable to material manufactured at IDT Fab 4, Hillsboro.

Please contact your local IDT sales representative to request samples or additional information.

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PRODUCT/PROCESS CHANGE NOTICE (PCN)

ATTACHMENT 2 - PCN #: L1301-01

TSMC Transfer Qualification Test Result Summary

Technology Information: 0.5 μm Fab Location: TSMC Fab 3

Technology Qualification Vehicle Test Summary - JESD47 Recommended Tests

Test / Conditions	Lead Vehicle: LVC16244A (40056X) Sample Size / Rejects/ each lot
High Temperature Operating Life (Dynamic) JESD22-A108B, +125°C @ 1000 hours or equivalent	79 / 0
Temperature Cycle JESD22-A104B, -55°C -/125°C, 1000 cycles	45 / 0
High Temperature Storage Bake JESD22-A-103-B, 150°C, 1000 hrs	77 / 0
ESD: Human Body Model JESD22-A114F, >2000V	5 / 0
ESD: Charged Device Model JEDEC 22-101C,>500V	5 / 0
ESD: Machine Model JESD22-A115B, >200V	5 / 0
Latch-up JESD78B	6 / 0
Electrical Characterization per Datasheet conditions	5 / 0

Technology Qualification Vehicle Test Summary - Supplemental Tests

Test / Conditions	Lead Vehicle: : LVC16244A (40056X) Sample Size / Rejects/ each lot
Ball Shear Test JESD22-B116-A, Ball Shear Strength > 5.7g	5 / 0
Highly Accelerated Stress Test (HAST) EIA/JESD22-A110B, 130°C/85%R.H. Vcc max for 100 hours.	45 / 0
Autoclave EIA/JESD22-A102C, 168hrs @ 2 ATM, Saturated Steam @ 121°C	45 / 0

Note: For HAST, Autoclave and Temperature Cycle, samples have been subjected to pre-conditioning per JESD22-Al 13